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result set*DB=USPT; PLUR=YES; OP=OR*L11 627488712 L11*DB=TDBD; PLUR=YES; OP=OR*L10 L90 L10*DB=DWPI; PLUR=YES; OP=OR*L9 L80 L9*DB=EPAB; PLUR=YES; OP=OR*L8 L70 L8*DB=JPAB; PLUR=YES; OP=OR*L7 L60 L7*DB=PGPB; PLUR=YES; OP=OR*L6 L50 L6*DB=USPT; PLUR=YES; OP=OR*L5 L4 and ldd and offset2 L5L4 L3 and "double gate"10 L4L3 L2 and ("second transistor" or "second tft")63 L3L2 L1 and ("first transistor" or "first tft")84 L2L1 electroluminescence3897 L1

END OF SEARCH HISTORY